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Two stage ELO GaN growth (ELO 2S); 2.4.7. GaN growth using pendeo-epitaxy; 2.4.8. Nano epitaxy; 2.5. Bulk nitride substrates
2.5.1. HNPS (high nitrogen pressure solution method) for the fabrication of crystalline GaN; 2.5.2. Ammonothermal synthesis of GaN; 2.5.3. Halide vapor phase epitaxy (HVPE) of GaN; 2.6. Conclusion; 2.7. Bibliography; Chapter 3. III-Nitride High-Brightness Light-Emitting Diodes; 3.1. Introduction; 3.2. p-n junction in GaN; 3.3. Active region: InGaN/GaN quantum well; 3.3.1. Growth and structure; 3.3.2. Optical properties; 3.4. Radiative efficiency; 3.5. Conclusion and prospects; 3.6. Bibliography; Chapter 4. Diode Processing; 4.1. Introduction; 4.2. Orders of magnitude; 4.3. Diode configurations
4.3.1. Conventional chip (CC); 4.3.2. Flip chip (FC); 4.3.3. Vertical thin film (VTF); 4.3.4. Thin film flip chip (TFFC); 4.4. Light extraction at wafer level; 4.5. Diode processing, etching, contact deposition; 4.5.1. N-type contacts; 4.5.2. P-type contacts; 4.6. Etching; 4.7. Substrate removal; 4.8. Potential evolutions; 4.9. Bibliography; Chapter 5. Packaging; 5.1. Introduction; 5.2. Different packaging processes; 5.2.1. Historical background; 5.2.2. From the wafer to the chip; 5.2.3. Components with connection pins; 5.2.4. SMT leadform components; 5.2.5. SMT "leadless" components
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5.6. Conclusion and trends

Sommario/riassunto

Light Emitting Diodes (LEDs) are no longer confined to use in commercial signage and have now moved firmly, and with unquestioned advantages, into the field of commercial and domestic lighting. This development was prompted in the late 1980s by the invention of the blue LED, a wavelength that had previously been missing from the available LED spectrum and which opened the way to providing white light. Since that point, LED performance (including energy efficiency) has improved dramatically, and now compares with the performance of fluorescent lights - and there remain further performance impro
